

N-channel silicon junction field-effect transistors Rev. 4 — 15 September 2011 Proc

Product data sheet

Product profile 1.

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage (max. 2.2 V for BF545A).

1.3 Applications

- Impedance converters in e.g. electret microphones and infra-red detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage		-	-	±30	V
V _{GSoff}	gate-source cut-off voltage	$I_D = 1 \ \mu A; \ V_{DS} = 15 \ V$	-0.4	-	-7.8	V
I _{DSS} drain current		$V_{GS} = 0 V; V_{DS} = 15 V$				
		BF545A	2	-	6.5	mA
		BF545B	6	-	15	mA
		BF545C	12	-	25	mA
P _{tot}	total power dissipation	$T_{amb} \leq 25 \ ^{\circ}C$	-	-	250	mW
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	3	-	6.5	mS



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2. Pinning information

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)		g → s
3	gate (g)		sym054

3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BF545A	-	plastic surface mounted package; 3 leads	SOT23		
BF545B					
BF545C					

4. Marking

Table 4. Marking	
Type number	Marking code ^[1]
BF545A	20*
BF545B	21*
BF545C	22*

[1] * = p: made in Hong Kong.

* = t: made in Malaysia.

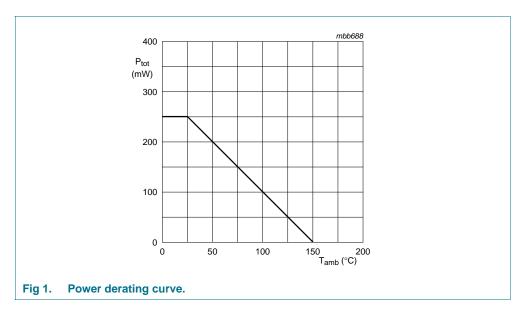
* = W: made in China.

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5. Limiting values

Table 5. In accorda	Limiting values nce with the Absolute Maximum	n Rating System (IE	EC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage (DC)		-	±30	V
V _{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
l _G	forward gate current (DC)		-	10	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².



6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

 Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

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7. Static characteristics

Table	7.	Static	chara	cteristi	cs	

T_i =	= 25	°C unless	otherwise	specified.
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)GSS}	gate-source breakdown voltage	$I_G = -1 \ \mu A; \ V_{DS} = 0 \ V$	-30	-	-	V
V _{GSoff} gate-source cut-off voltage		$I_D = 200 \ \mu A; \ V_{DS} = 15 \ V$				
		BF545A	-0.4	-	-2.2	V
	BF545B	-1.6	-	-3.8	V	
		BF545C	-3.2	-	-7.8	V
		$I_D = 1 \ \mu A; \ V_{DS} = 15 \ V$	-0.4	-	-7.5	V
I _{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF545A	2	-	6.5	mA
		BF545B	6	-	15	mA
		BF545C	12	-	25	mA
I _{GSS}	gate-source leakage current	V_{GS} = -20 V; V_{DS} = 0 V	-	-0.5	-1000	pА
	V_{GS} = -20 V; V_{DS} = 0 V; T _j = 125 °C	-	-	-100	nA	
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 15 \text{ V}$	3	-	6.5	mS
y _{os}	common source output admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	40	-	μS

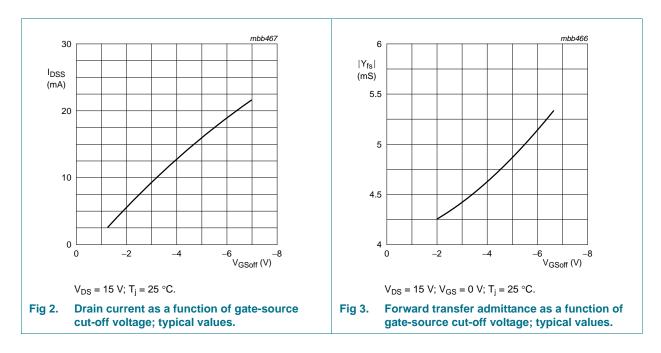
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8. Dynamic characteristics

Table 8. Dynamic characteristics

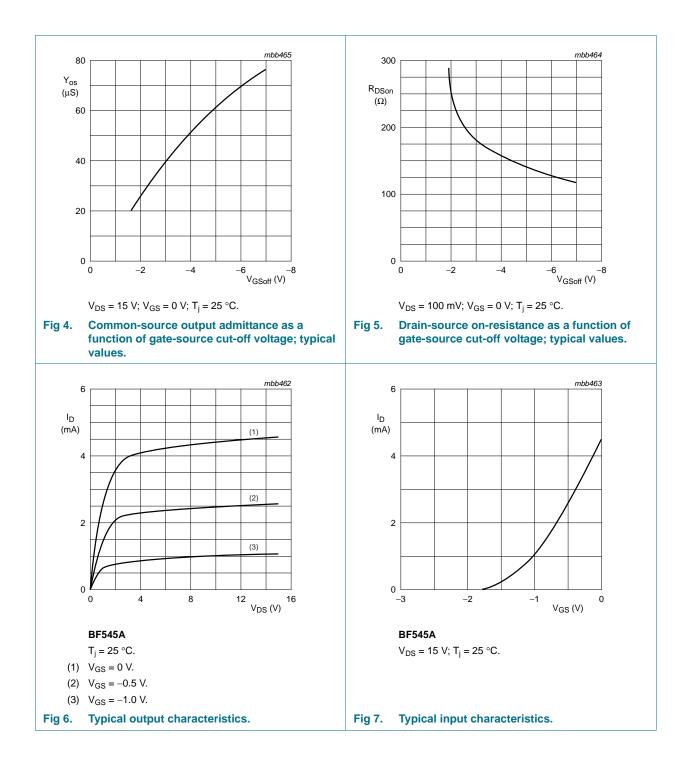
 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz				
		$V_{GS} = -10 V$	-	1.7	-	pF
		$V_{GS} = 0 V$	-	3	-	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 15 V; f = 1 MHz				
		$V_{GS} = -10 V$	-	0.8	-	pF
	$V_{GS} = 0 V$	-	0.9	-	pF	
g _{is} common source input	V _{DS} = 10 V; I _D = 1 mA					
	conductance	f = 100 MHz	-	15	-	μS
		f = 450 MHz	-	300	-	μS
g fs	common source transfer	$V_{DS} = 10 \text{ V}; \text{ I}_{D} = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	2	-	mS
		f = 450 MHz	-	1.8	-	mS
g _{rs}	common source reverse	V _{DS} = 10 V; I _D = 1 mA				
	conductance	f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
g _{os}	common source output	V _{DS} = 10 V; I _D = 1 mA				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS



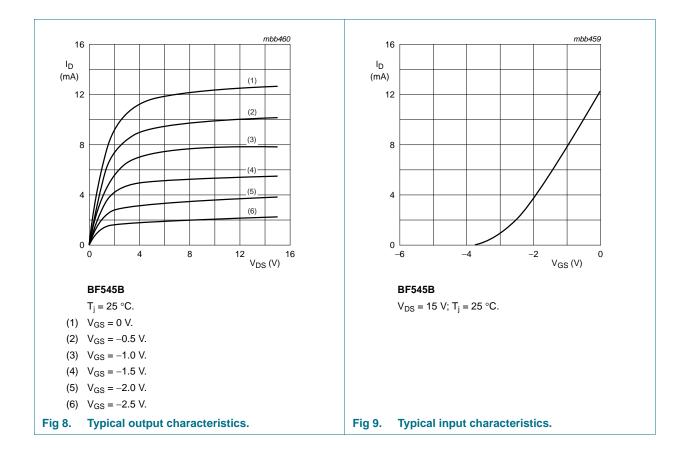
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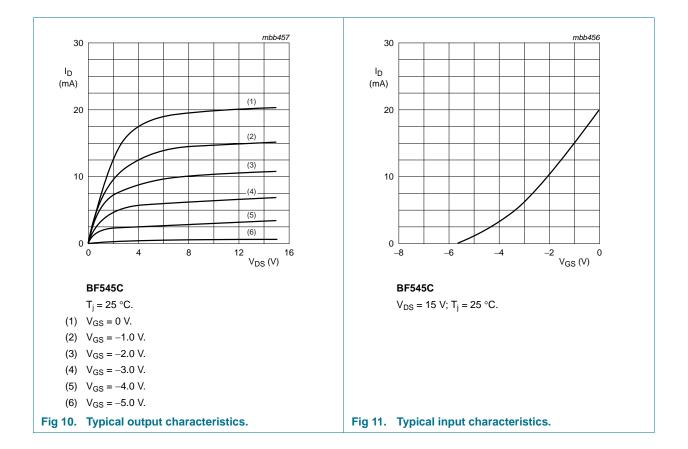


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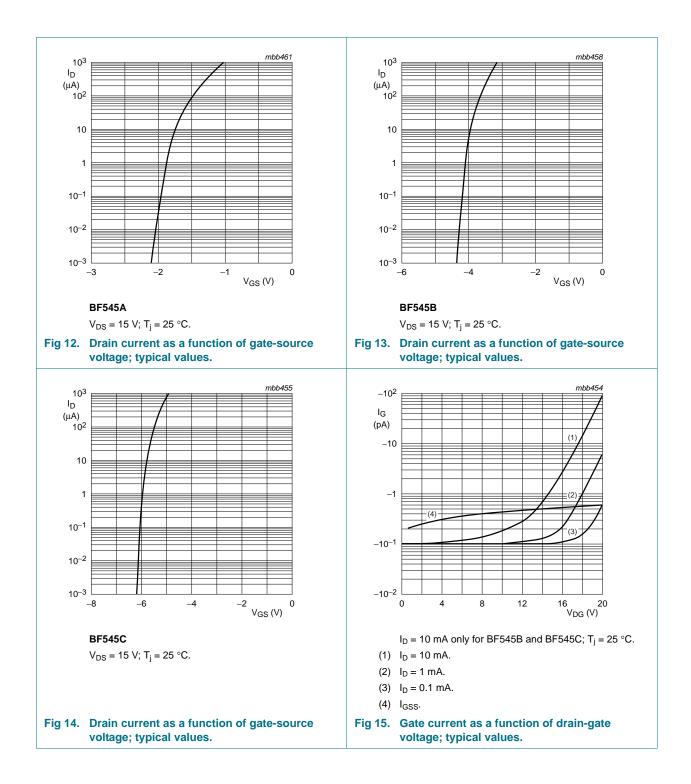


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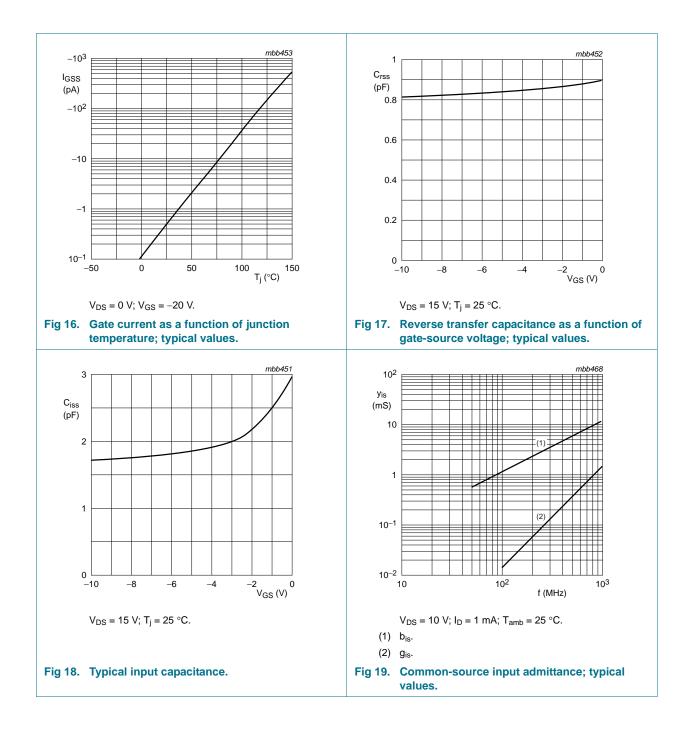
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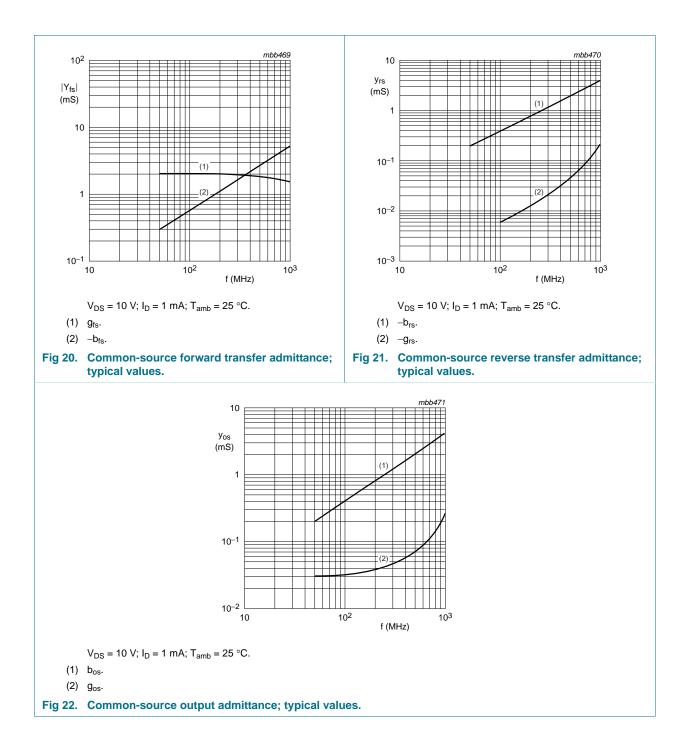
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BF545A; BF545B; BF545C



BF545A_BF545B_BF545C

BF545A; BF545B; BF545C



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9. Package outline

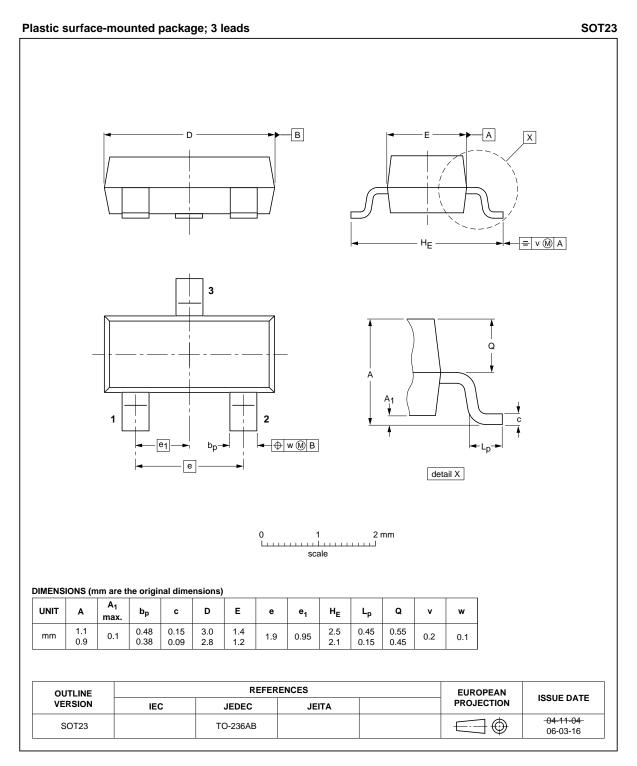


Fig 23. Package outline.

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10. Revision history

Table 9.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BF545A_BF545B_BF545C v.4	20110915	Product data sheet	-	BF545A_BF545B_BF545C v.3
Modifications:		of this data sheet has be of NXP Semiconductors.	0	comply with the new identity
	 Legal texts 	have been adapted to th	ie new company n	ame where appropriate.
	 Package ou 	Itline drawings have bee	n updated to the la	atest version.
BF545A_BF545B_BF545C v.3 (9397 750 13391)	20040805	Product data sheet	-	BF545A-B-C v.2
BF545A-B-C v.2	19960729	Product specification	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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